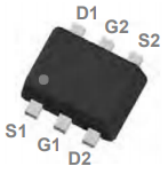
Features

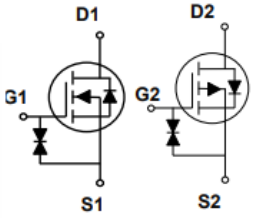
- *Low $R_{DS(on)}$ @V_{GS}=4.5V*
- *2.5V Logic Level Control*
- *SOT563 Package*
- *Pb−Free, RoHS Compliant*

Applications

- *LED Lighting Application*
- *ON/OFF switch*
- *Networking*

V_{DS}	20	-20	V
$R_{DS(on),TYP}$@ V_{GS}=±4.5 V	200	510	mΩ
$R_{DS(on),TYP}$@ V_{GS}=±3.3V	220	570	mΩ
$I_{D\ Max}$	1	-0.6	A





Order Information

SOT563

Product	Package	Marking	Packing
DMC2400UV-7-CN	SOT563	21	3000PCS/Reel

Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Symbol	Parameter		Rating		Unit
			NMOS	PMOS	
V_{GS}	Gate-Source Voltage		±8	±8	V
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage		20	-20	V
T_{STG} T_J	Storage and operating temperature range		-55 to 150		°C
I_S	Diode Continuous Forward Current	T_A=25°C	1	-0.6	A
Mounted on Large Heat Sink					
I_{DM}	Pulse Drain Current Tested①	T_A=25°C	4	-2.4	A
I_D	Continuous Drain Current	T_A=25°C	1	-0.6	A
		T_A=70°C	0.8	-0.48	
P_D	Power dissipation for Dual Operation	T_A=25°C	0.3		W
		T_A=70°C	0.2		
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		400		°C/W

N-Channel Electrical Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	20	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current(T_A=25℃)	V_{DS}=20V, V_{GS}=0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T_A=125℃)	V_{DS}=16V, V_{GS}=0V	--	--	100	nA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±8V, V_{DS}=0V	--	--	±10	uA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	0.35	0.6	1.0	V
$R_{DS(ON)}$	Drain-Source On-State Resistance②	V_{GS}=4.5V, I_D=0.5A	--	200	300	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance②	V_{GS}=3.3V, I_D=0.3A	--	220	350	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance②	V_{GS}=2.5V, I_D=0.2A	--	250	400	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	V_{DS}=10V, V_{GS}=0V, f=1MHz	--	36	--	pF
C_{oss}	Output Capacitance		--	9.3	--	pF
C_{rss}	Reverse Transfer Capacitance		--	6.8	--	pF
Q_g	Total Gate Charge	V_{DS}=10V I_D=0.5A, V_{GS}=4.5V	--	0.8	--	nC
Q_{gs}	Gate Source Charge		--	0.11	--	nC
Q_{gd}	Gate Drain Charge		--	0.18	--	nC
Switching Characteristics@ T_J = 25°C (unless otherwise stated)						
$t_{d(on)}$	Turn on Delay Time	V_{DD}=10V, I_D=0.5A, R_G=3.3Ω, V_{GS}=4.5V	--	7	--	ns
t_r	Turn on Rise Time		--	10	--	ns
$t_{d(off)}$	Turn Off Delay Time		-	35	--	ns
t_f	Turn Off Fall Time		--	14	--	ns
Source Drain Diode Characteristics@ T_J = 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage②	I_{SD}=0.3A, V_{GS}=0V	--	0.74	1.2	V

P-Channel Electrical Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=-250μA	-20	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current(T_A=25℃)	V_{DS}=-20V, V_{GS}=0V	--	--	-1	μA
	Zero Gate Voltage Drain Current(T_A=125℃)	V_{DS}=-16V, V_{GS}=0V	--	--	-100	nA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±8V, V_{DS}=0V	--	--	±10	uA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250μA	-0.35	-0.6	-1.0	V
$R_{DS(ON)}$	Drain-Source On-State Resistance②	V_{GS}=-4.5V, I_D=-0.5A	--	510	650	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance②	V_{GS}=-4.5V, I_D=-0.3A	--	570	700	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance②	V_{GS}=-4.5V, I_D=-0.1A	--	600	800	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	V_{DS}=-10V, V_{GS}=0V, f=1MHz	--	39	--	pF
C_{oss}	Output Capacitance		--	6.4	--	pF
C_{rss}	Reverse Transfer Capacitance		--	4.2	--	pF
Q_g	Total Gate Charge	V_{DS}=-10V I_D=-0.5A, V_{GS}=-4.5V	--	1.1	--	nC
Q_{gs}	Gate Source Charge		--	0.1	--	nC
Q_{gd}	Gate Drain Charge		--	0.3	--	nC
Switching Characteristics@ T_J = 25°C (unless otherwise stated)						
$t_{d(on)}$	Turn on Delay Time	V_{DD}=-10V, I_D=-0.5A, R_G=3.3Ω, V_{GS}=-4.5V	--	16	--	ns
t_r	Turn on Rise Time		--	32	--	ns
$t_{d(off)}$	Turn Off Delay Time		-	85	--	ns
t_f	Turn Off Fall Time		--	68	--	ns
Source Drain Diode Characteristics@ T_J = 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage②	I_{SD}=-0.3A, V_{GS}=0V	--	-0.89	-1.2	V

Notes:

① Pulse width limited by maximum allowable junction temperature

②Pulse test ; Pulse width≤300μs, duty cycle≤2%.

Typical Characteristics: N Channel

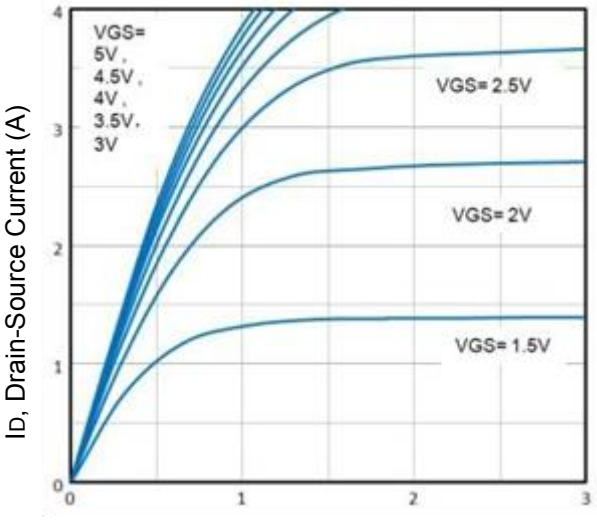


Fig1. Typical Output Characteristics

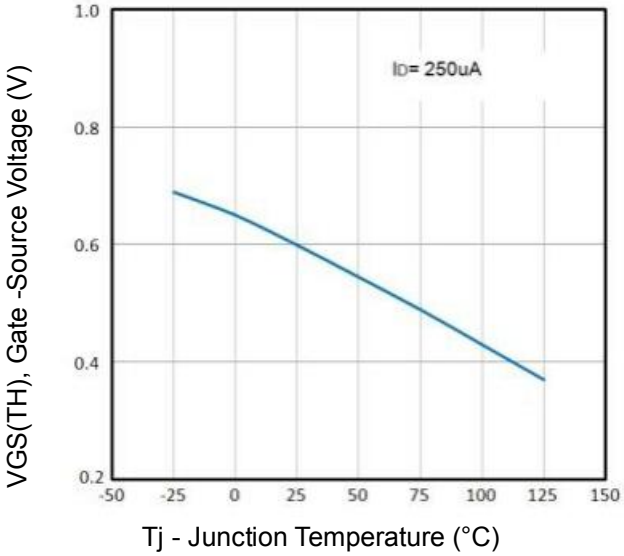


Fig2. Normalized Threshold Voltage Vs. Temperature

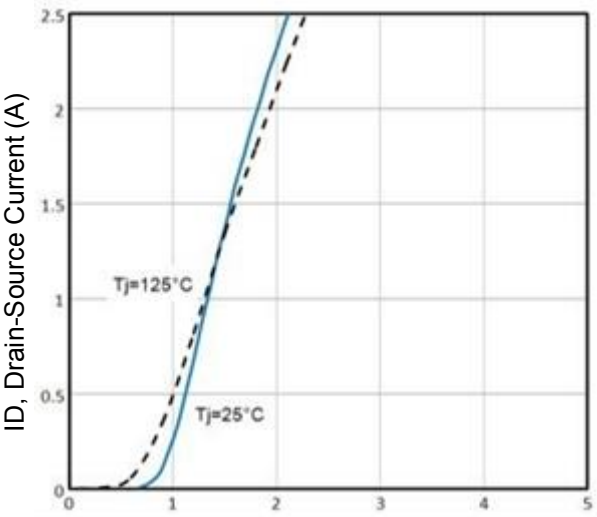


Fig3. Typical Transfer Characteristics

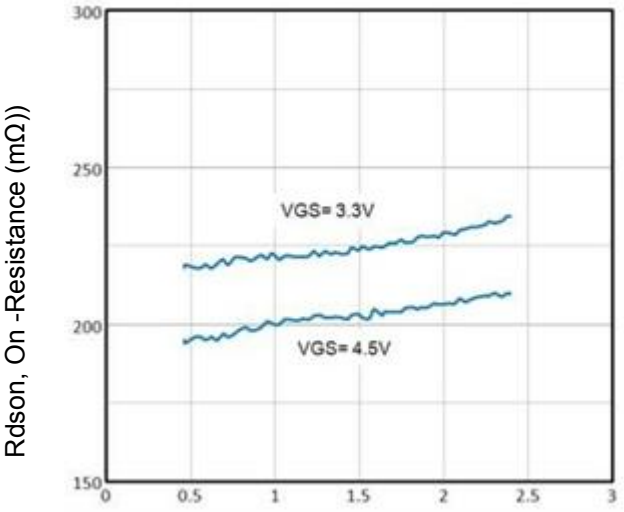


Fig4. On-Resistance vs. Drain Current and Gate

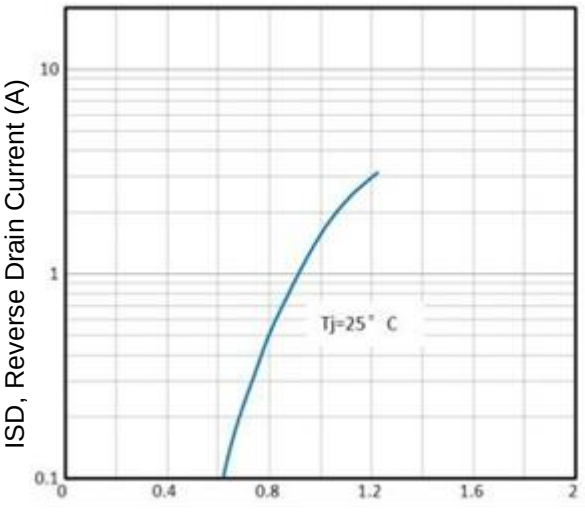


Fig5. Typical Source-Drain Diode Forward Voltage

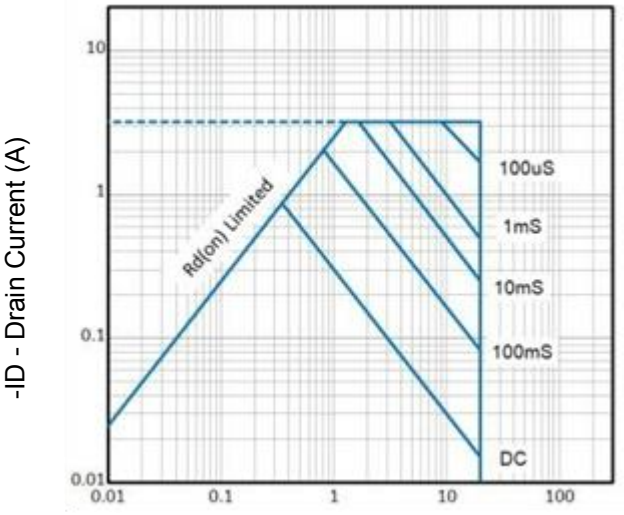


Fig6. Maximum Safe Operating Area

Typical Characteristics: N-Channel

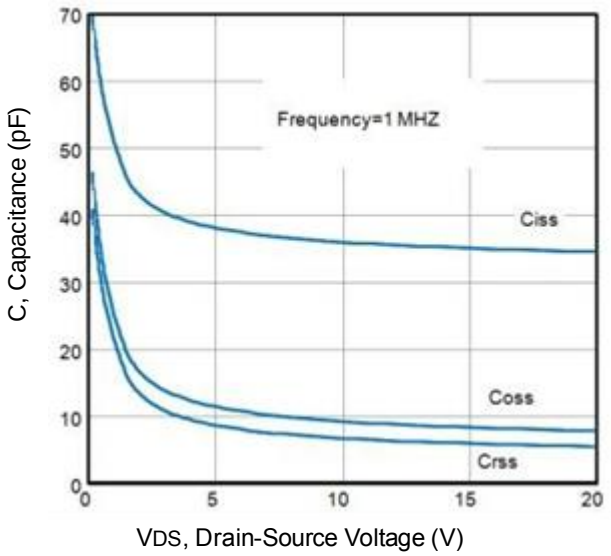


Fig7. Typical Capacitance Vs. Drain-Source Voltage

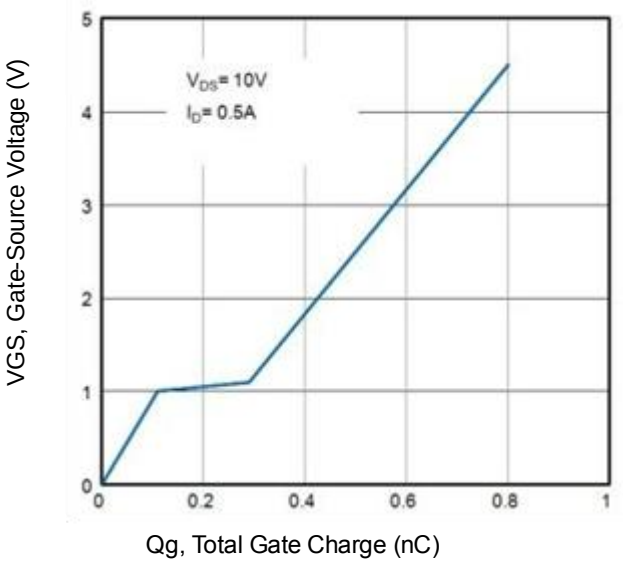


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

Typical Characteristics: P-Channel

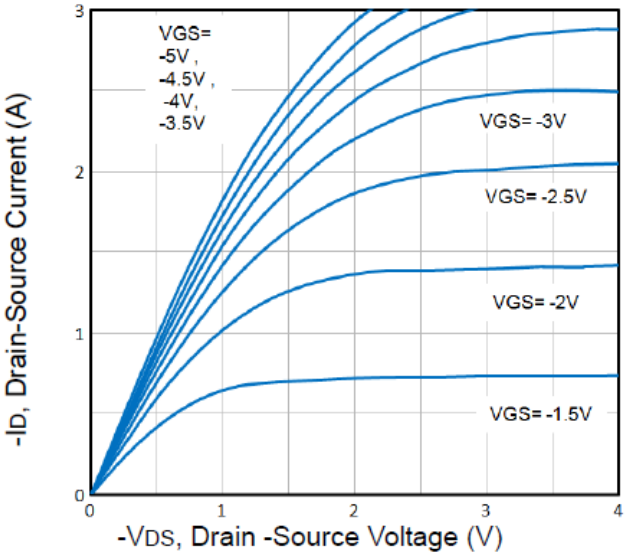


Fig1. Typical Output Characteristics

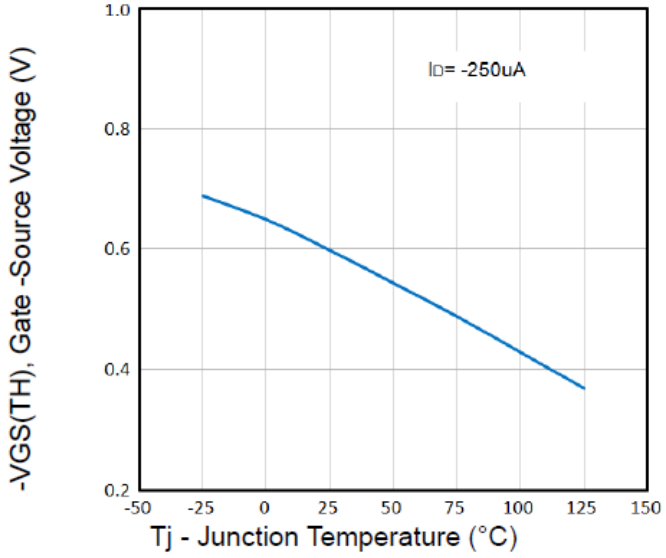


Fig2. Normalized Threshold Voltage Vs. Temperature

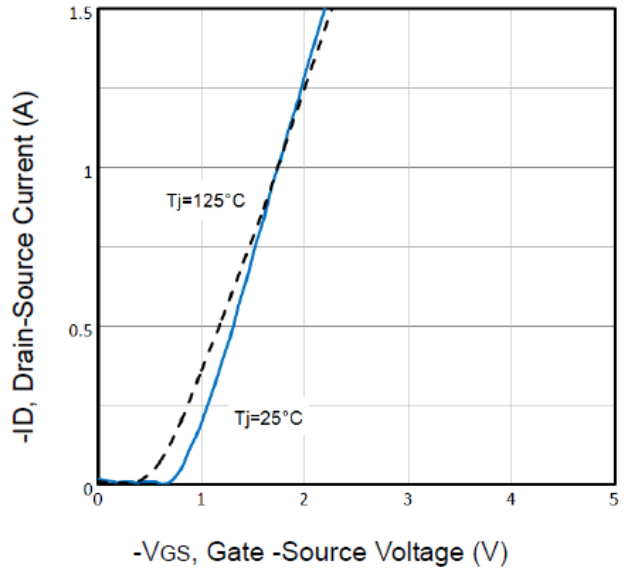


Fig3. Typical Transfer Characteristics

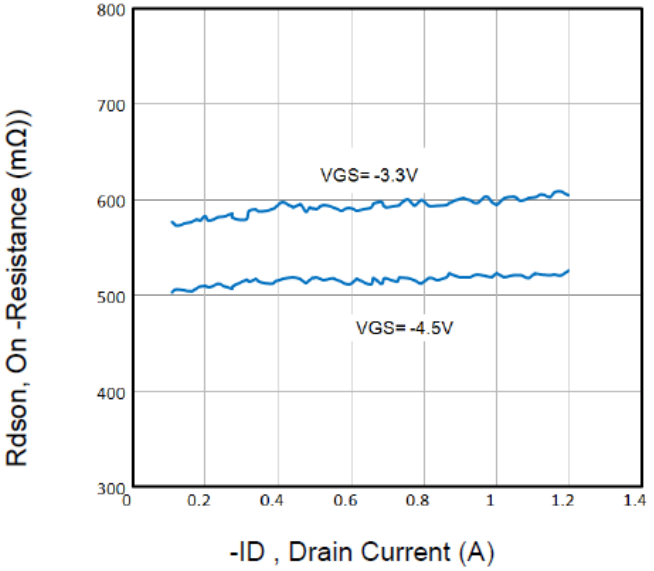


Fig4. On-Resistance vs. Drain Current and Gate

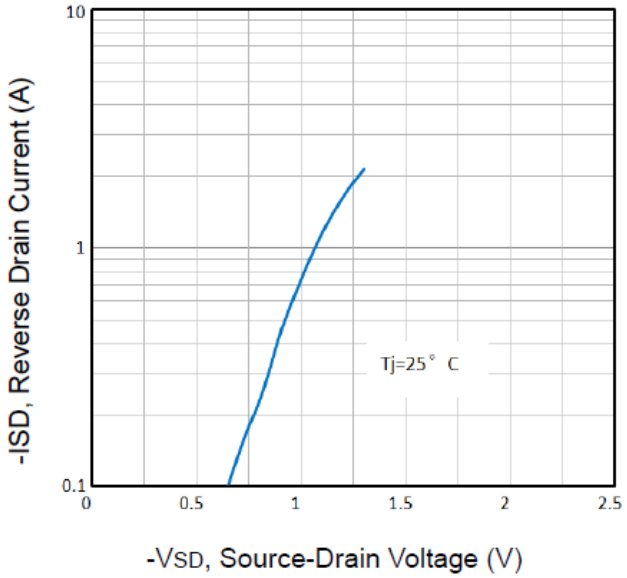


Fig5. Typical Source-Drain Diode Forward Voltage

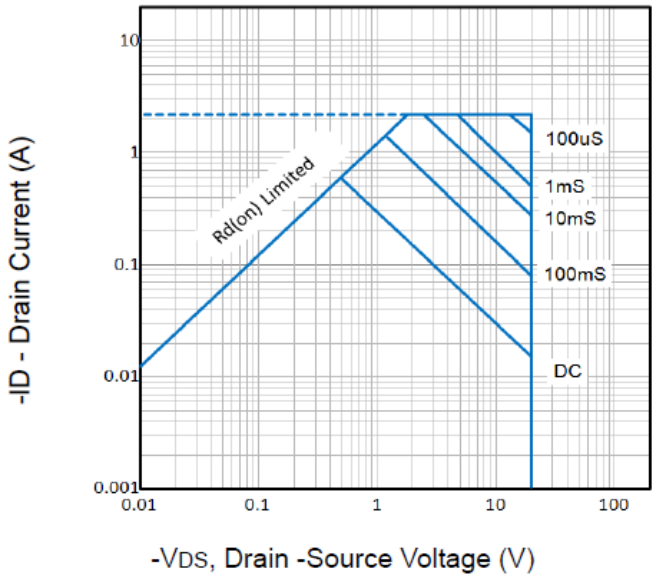


Fig6. Maximum Safe Operating Area

Typical Characteristics: P-Channel

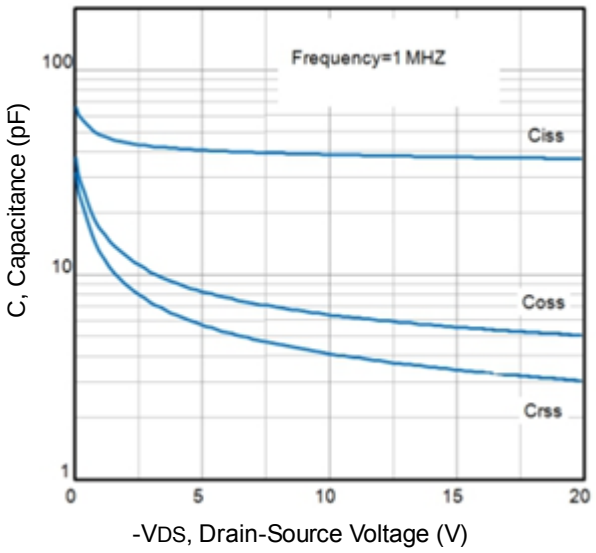


Fig7. Typical Capacitance Vs. Drain-Source Voltage

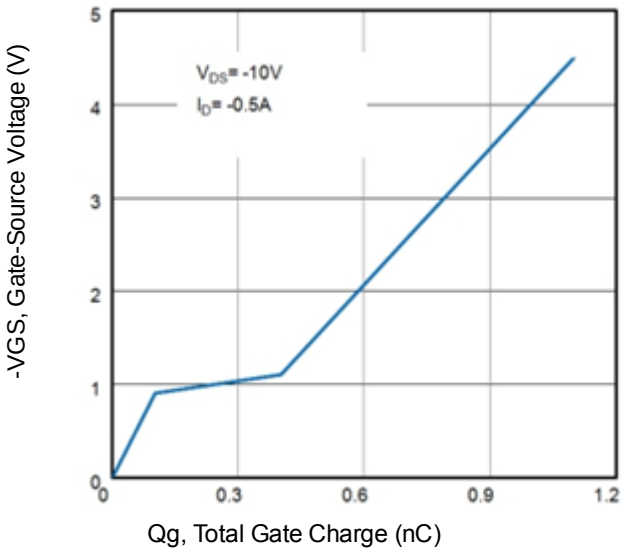
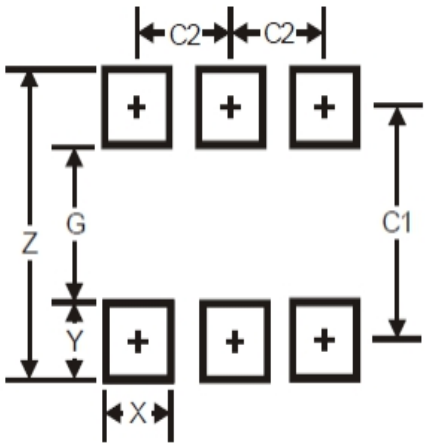
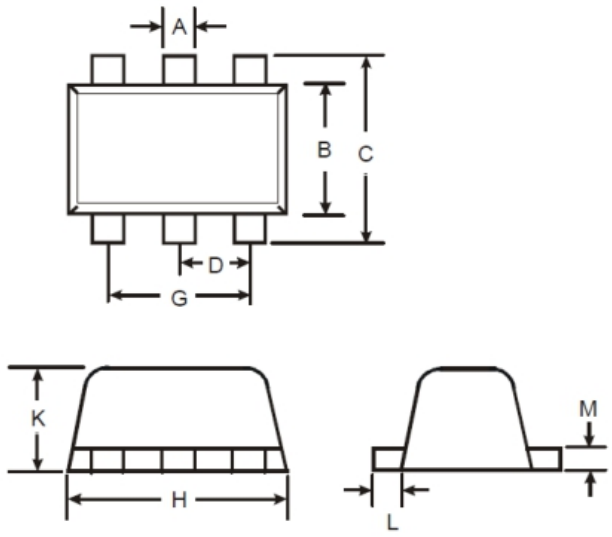


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

SOT563 Mechanical Data



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5



SOT563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

NOTICE

The information presented in this document is for reference only. Involving product optimization and productivity improvement, ChipNobo reserves the right to adjust product indicators and upgrade some technical parameters. ChipNobo is entitled to be exempted from liability for any delay or non-delivery of the information disclosure process that occurs.
本文件中提供的信息仅供参考。涉及产品优化和生产效率改善，ChipNobo 有权调整产品指标和部分技术参数的升级，所出现信息披露过程存在延后或者不能送达的情形，ChipNobo 有获免责权。

The product listed herein is designed to be used with residential and commercial equipment, and do not support sensitive items and specialized equipment in areas where sanctions do exist. ChipNobo Co., Ltd or anyone on its behalf, assumes no responsibility or liability for any damages resulting from improper use.
此处列出的产品旨在民用和商业设备上使用，不支持确有制裁地区的敏感项目和特殊设备，ChipNobo 有限公司或其代表，对因不当使用而造成的任何损害不承担任何责任。

For additional information, please visit our website http://www.chipnobo.com, or consult your nearest Chipnobo sales office for further assistance.
欲了解更多信息，请访问我们的网站 http://www.chipnobo.com，或咨询离您最近的 Chipnobo 销售办事处以获得进一步帮助。